

 **PALM INTRANET**Day : Friday
Date: 9/8/2006
Time: 16:11:18

Inventor Information for 10/500239

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| US 20050182328 A1 | US- PGPUB | 20050818 | System enabling chromaticity measurement in the visible and invisible ranges | 600/476 | | Matsumoto, Kazuji et al. |
| US 20050142654 A1 | US- PGPUB | 20050630 | Slide glass, cover glass and pathologic diagnosis system | 435/287.1 | 359/885 | Matsumoto, Kazuji et al. |
| US 20050106744 A1 | US- PGPUB | 20050519 | Optical analysis for heterogeneous medium | 436/164 | | Mizushima, Yoshihiko et al. |
| US 20020082504 A1 | US- PGPUB | 20020627 | Optical analysis method for inhomogeneous turbid media | 600/477 | 356/342 | Mizushima, Yoshihiko et al. |
| US 6643020 B2 | USPAT | 20031104 | Optical analysis method for inhomogeneous turbid media | 356/432 | 600/310; 600/322 | Mizushima; Yoshihiko et al. |
| US 5717627 A | USPAT | 19980210 | Optical memory device incorporating photodetector devices and light emitting devices | 365/112 | 250/205; 257/E31.097; 365/115; 365/175 | Mizushima; Yoshihiko |
| US 5534992 A | USPAT | 19960709 | Optical measuring apparatus | 356/5.1 | 356/5.09 | Takeshima; Akira et al. |
| US 5336902 A | USPAT | 19940809 | Semiconductor photo-electron-emitting device | 257/10 | 257/11; 257/453; 257/459; 257/622; 313/542 | Nigaki; Minoru et al. |
| US 5227638 A | USPAT | 19930713 | Method and apparatus for evaluating luminous efficiency | 250/484.2 | 250/458.1; 250/459.1 | Mizushima; Yoshihiko et al. |
| US 5138191 A | USPAT | 19920811 | Photoemitter | 327/514 | 257/21; 257/54; 257/9; 313/542 | Mizushima; Yoshihiko et al. |
| US 5109358 A | USPAT | 19920428 | Optical flip-flop circuit | 365/154 | 250/214DC; 365/112; 365/215; 365/64; 365/73 | Mizushima; Yoshihiko et al. |
| US 5082273 A | USPAT | 19920121 | Slip storing apparatus | 271/215 | 271/181; 83/94 | Matsumoto; Kazuji et al. |
| US 5068815 A | USPAT | 19911126 | Optical full adder | 708/191 | 708/670 | Mizushima; Yoshihiko et al. |
| US 5051573 A | USPAT | 19910924 | Optical logic operation system | 250/214LS | 377/102 | Mizushima; Yoshihiko et al. |
| US 5044744 | USPAT | 19910903 | Method and apparatus for | 356/5.1 | 342/127; | Ogawa; |

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| A | | | distance measurement using electromagnetic waves | | 342/134 | Ichizo et al. |
| US 5034921 A | USPAT | 19910723 | High speed optical memory circuit | 365/112 | 365/215 | Nakajima; Kazutoshi et al. |
| US 5020064 A | USPAT | 19910528 | Electromagnetic wave device | 372/37 | | Mizushima; Yoshihiko et al. |
| US 4875093 A | USPAT | 19891017 | Ultrafast continuous imaging apparatus | 348/61 | 313/524; 313/542; 348/804; 348/901 | Koishi; Musubu et al. |
| US 4827317 A | USPAT | 19890502 | Time interval measuring device | 356/73.1 | 250/214VT; 356/5.01; 368/120 | Mizushima; Yoshihiko et al. |
| US 4720734 A | USPAT | 19880119 | Low loss and high speed diodes | 257/484 | 257/485; 257/769; 257/E21.163; 257/E29.148; 257/E29.338 | Amemiya; Yoshihito et al. |
| US 4629486 A | USPAT | 19861216 | Process of how to fabricate the microchannel plate | 65/429 | 156/296; 65/406 | Uchiyama; Toshiyuki et al. |
| US 4587547 A | USPAT | 19860506 | Electrode structure for a semiconductor devices | 257/655 | 148/DIG.122; 148/DIG.140; 148/DIG.20; 257/136; 257/51; 257/657; 257/E23.012; 257/E29.037; 257/E29.146; 257/E29.148; 257/E29.327; 257/E29.336 | Amemiya; Yoshihito et al. |
| US 4521794 A | USPAT | 19850604 | Electrode and semiconductor device provided with the electrode | 257/63 | 257/754; 257/E21.166; 257/E23.164; 257/E29.146 | Murase; Katsumi et al. |
| US 4460417 A | USPAT | 19840717 | Method of manufacturing insulating film and electric device utilizing the same | 438/365 | 257/587; 257/63; 257/E21.301; 257/E21.375; 257/E29.173; 438/684; 438/770; 438/784 | Murase; Katsumi et al. |

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| US 4434224 A | USPAT | 19840228 | Method of pattern formation | 430/323 | 216/48; 216/49; 216/83; 257/E21.024; 257/E21.214; 257/E21.266; 257/E21.346; 430/312; 430/313; 430/314; 430/322; 430/324; 430/325; 430/326; 430/329; 430/330; 430/5 | Yoshikawa; Akira et al. |
| US 4414557 A | USPAT | 19831108 | Bipolar transistors | 257/49 | 257/198; 257/656; 257/E29.003; 257/E29.034; 257/E29.191; 257/E29.194 | Amemiya; Yoshihito et al. |
| US 4350541 A | USPAT | 19820921 | Doping from a photoresist layer | 438/559 | 257/E21.266; 438/551; 438/562; 438/930 | Mizushima; Yoshihiko et al. |
| US 4341954 A | USPAT | 19820727 | Photo-electric converting apparatus | 257/464 | 257/E27.141; 257/E31.009; 257/E31.065; 257/E31.067 | Mizushima; Yoshihiko et al. |
| US 4320191 A | USPAT | 19820316 | Pattern-forming process | 430/296 | 216/67; 257/E21.252; 257/E21.266; 427/504; 427/510; 430/313; 430/317; 430/323 | Yoshikawa; Akira et al. |
| US 4145121 A | USPAT | 19790320 | Light modulator | 385/2 | 359/276; 359/321 | Hata; Susumu et al. |
| US 4142200 A | USPAT | 19790227 | Semiconductor photodiodes | 257/438 | 257/463; 257/655; 257/E31.063 | Mizushima; Yoshihiko et al. |
| US 4127414 A | USPAT | 19781128 | Pattern-forming materials having a radiation sensitive chalcogenide layer and a | 430/270.1 | 430/313 | Yoshikawa; Akira et al. |

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| | | | method of forming patterns with such materials | | | |
| US 3845251 A | USPAT | 19741029 | IMPROVED ACOUSTIC-ELECTRO CONVERTING DEVICE HAVING SEMICONDUCTOR GRANULES | 381/175 | 381/179 | Takagi; Toru et al. |
| US 3816108 A | USPAT | 19740611 | SEMICONDUCTOR GRANULES FOR USE IN ACOUSTIC-ELECTRO CONVERTING DEVICES | 420/576 | 420/579 | Takagi; Toru et al. |
| US 3811074 A | USPAT | 19740514 | SEMICONDUCTOR DEVICE AND APPARATUS USING THE SAME | 257/212 | 257/443; 257/462; 257/E27.08; 327/438; 327/569; 327/574; 377/64 | Suzuki; Toshimasa et al. |
| US 3781806 A | USPAT | 19731225 | SEMICONDUCTOR SWITCHING ELEMENT AND A SEMICONDUCTOR SWITCHING INVOLVING THE SAME | 340/14.64 | 257/462; 257/560; 257/E27.08; 327/427 | Mizushima; Yoshihiko et al. |
| US 3657616 A | USPAT | 19720418 | SEMICONDUCTOR SWITCHING ELEMENT | 257/212 | 257/E27.08; 327/480; 327/481; 327/514; 340/14.62 | Mizushima; Yoshihiko et al. |
| US 3638082 A | USPAT | 19720125 | PNPN IMPATT DIODE HAVING UNEQUAL ELECTRIC FIELD MAXIMA | 257/110 | 257/155; 257/176; 257/482 | Mizushima; Yoshihiko et al. |
| US 3624430 A | USPAT | 19711130 | SELENIUM-TELLURIUM TRANSDUCER EMPLOYING PIEZORESISTANCE EFFECT | 338/2 | 252/62.9R; 257/417; 381/175; 73/776; 73/826 | Mizushima; Yoshihiko et al. |
| US 3469117 A | USPAT | 19690923 | ELECTRIC CIRCUIT EMPLOYING SEMICONDUCTOR DEVICES [TEXT AVAILABLE IN USOCR DATABASE] | 327/580 | | MIZUSHIMA YOSHIHIKO et al. |